

L Number	Hits	Search Text	DB	Time stamp
-	4	'gate oxide' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/22 07:29
-	7	@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 15:33
-	1	@ad<=20020219 and 'ONO' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 08:28
-	10	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 08:32
-	52	(438/954).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:24
-	245	(438/593).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:26
-	627	(438/770).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:31
-	481	(438/264).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:27
-	208	(438/594).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:27
-	518	(438/275).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 15:32
-	323	(438/199).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:28
-	91	(438/477).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:28
-	77	(438/216).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:28
-	577	(438/287).ccls. and @ad<=20020119	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/24 13:29

	27	@ad<=20020219 and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/26 12:07
	2	@ad<=20020219 and 'low pressure rapid thermal process'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/26 12:17
	416	@ad<=20020219 and 'TFT' and 'ONO'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/27 07:12
	71	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/22 08:16
	2	("6525384").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/22 09:48
	2	"20030155582"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:45
	2	'TFT' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 10:04
	2	("5700699").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:59
	1	'TFT' and 'free radical enhanced rapid thermal oxidation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 10:32
	131	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:25
	121	@ad<=20020219 and 'SONOS' and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:34
	120	@ad<=20020219 and 'SONOS' same 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:14
	1	@ad<=20020219 and 'SONOS device' same 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 12:30
	1	@ad<=20020219 and 'SONOS device' same 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 12:31

	121	@ad<=20020219 and 'thin film transistor' same 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:16
	120	@ad<=20020219 and 'TFT' and 'in-situ steam generation' or 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:17
	1	@ad<=20020219 and 'TFT' and ('in-situ steam generation' or 'ISSG')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:17
	37	@ad<=20020219 and 'SONOS device'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:18
	2	@ad<=20020219 and 'SONOS device' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:18
	1	"6319775".PN.	USPAT	2004/05/27 13:19
	1	"6309927".PN.	USPAT	2004/05/27 13:22
	1	"6309927".PN.	USPAT	2004/05/27 13:23
	1	"6248628".PN.	USPAT	2004/05/27 13:23
	1	"6171900".PN.	USPAT	2004/05/27 13:25
	1	@ad<=20020219 and 'in-situ steam generation' same 'SONOS' with 'device'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:26
	1	@ad<=20020219 and 'in-situ steam generation' same 'SONOS'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:26
	3	@ad<=20020219 and 'SONOS' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:26
	2	@ad<=20020219 and 'SONOS' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:27
	1	@ad<=20020219 and 'TFT' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:27
	39777	@ad<=20020219 and 'Thin film transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:29
	13	'SONOS' same 'device' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/27 13:44

-	14	'SONOS' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:45
-	3	'SONOS' and 'ISSG' with 'process'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:45
-	2	'TFT' and 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:45
-	2	'TFT' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:45
-	238	@ad<=20020219 and 'bottom gate TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 15:32
-	1	@ad<=20020219 and 'tunnel oxide' same 'ISSG'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 15:34